

NPN Epitaxial Silicon Transistor

KSP42, KSP43

Features

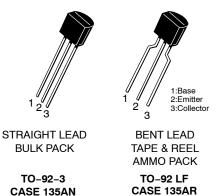
- Collector-Emitter Voltage:
 - ◆ KSP42: V_{CEO} = 300 V
 - ♦ KSP43: V_{CEO} = 200 V
- Collector Dissipation: P_C (max.) = 625 mW
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS

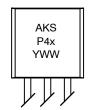
Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage KSP42		300	V
		KSP43	200	
V _{CEO}	Collector-Emitter Voltage	KSP42	300	V
		KSP43	200	
V _{EBO}	Emitter-Base Voltage		6	V
I _C	Collector Current		500	mA
P _C	Collector Power Dissipation	625	mW	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature		-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



MARKING DIAGRAM



A = Assembly Code

KSP4x = Device Code (x = 2 or 3)

Y = Year WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

KSP42, KSP43

ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping
KSP42BU	KSP42	TO-92-3 (Pb-Free), case 135AN	10,000 units / Bulk Bag
KSP42TA	KSP42	TO-92-3 (Pb-Free), case 135AR	2,000 units / Fan–Fold
KSP43TA	KSP43	TO-92-3 (Pb-Free), case 135AR	2,000 units / Fan–Fold

DISCONTINUED (Note 1)

KSP43BU	KSP43	TO-92-3 (Pb-Free), case 135AN	10,000 units / Bulk Bag

^{1.} **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

ELECTRICAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter		Conditions	Min	Max	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	KSP42	$I_C = 100 \mu A, I_E = 0$	300		V
		KSP43		200		1
BV _{CEO}	Collector-Emitter Breakdown Voltage	KSP42	I _C = 1 mA, I _B = 0	300		V
	(Note 2)	KSP43		200		
BV _{EBO}	Emitter-Base Breakdown Voltage		$I_E = 100 \mu A, I_C = 0$	6		V
I _{CBO}	Collector Cut-Off Current	KSP42	V _{CB} = 200 V, I _E = 0		100	nA
		KSP43	V _{CB} = 160 V, I _E = 0		100	
I _{EBO}	Emitter Cut-Off Current	KSP42	V _{EB} = 6 V, I _C = 0		100	nA
		KSP43	V _{EB} = 4 V, I _C = 0		100	
h _{FE}	DC Current Gain (Note 2)		V _{CE} = 10 V, I _C = 1 mA	25		
			V _{CE} = 10 V, I _C = 10 mA	40		
			V _{CE} = 10 V, I _C = 30 mA	40		
V _{CE} (sat)	Collector-Emitter Saturation Voltage (Note 2)		I _C = 20 mA, I _B = 2 mA		0.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage (Note 2)		I _C = 20 mA, I _B = 2 mA		0.9	V
Cob	Output Capacitance	KSP42	V _{CB} = 20 V, I _E = 0, f = 1 MHz		3	pF
		KSP43			4	1
f _T	Current Gain Bandwidth Product		V _{CE} = 20 V, I _C = 10 mA, f = 100 MHz	50		MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse test: pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$.

KSP42, KSP43

TYPICAL PERFORMANCE CHARACTERISTICS

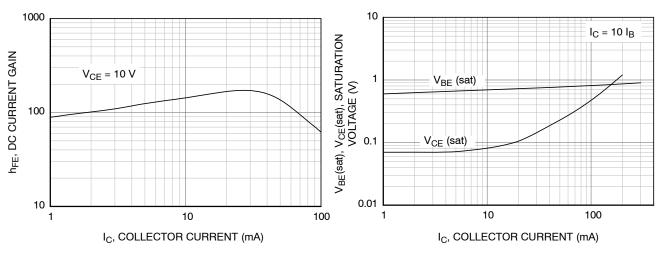


Figure 1. DC Current Gain

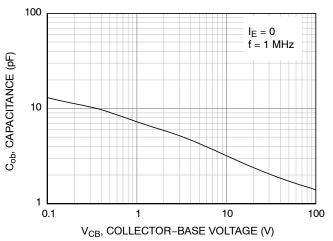


Figure 3. Current Gain Bandwidth Product

Figure 2. Collector–Emitter Saturation Voltage and Base–Emitter Saturation Voltage

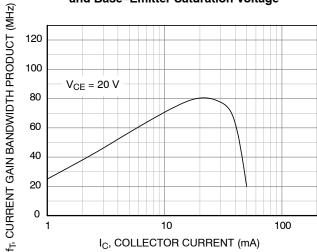
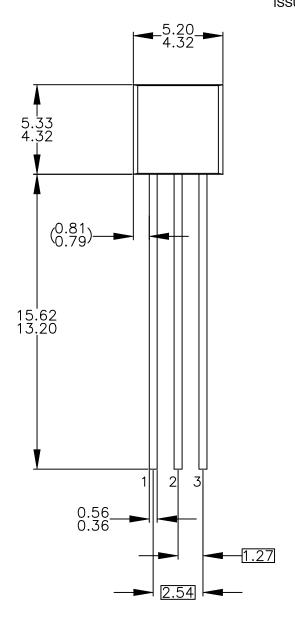


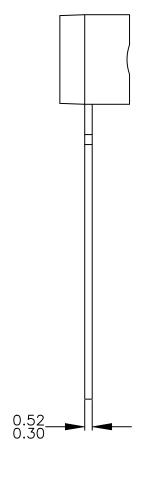
Figure 4. Current Gain Bandwidth Product



TO-92 3 4.825x4.76 CASE 135AN ISSUE O

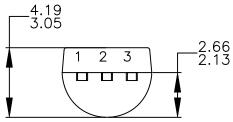
DATE 31 JUL 2016





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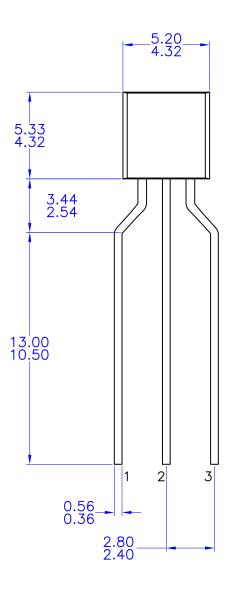


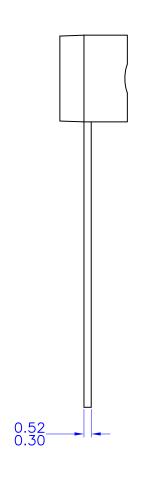


TO-92 3 4.83x4.76 LEADFORMED

CASE 135AR ISSUE O

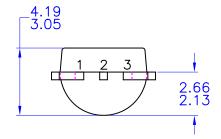
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